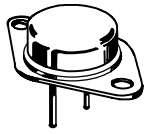
High-Current Complementary Silicon Power Transistors

. . . designed for use in high−power amplifier and switching circuit applications.

- High Current Capability −
  I_C Continuous = 50 Amperes.
- DC Current Gain −
  h_{FE} = 15−60 @ I_C = 25 Adc
- Low Collector−Emitter Saturation Voltage −
  $V_{CE(sat)}$ = 1.0 Vdc (Max) @ I_C = 25 Adc
- **These devices are available in Pb−free package(s). Specifications herein apply to both standard and Pb−free devices. Please see our website at www.onsemi.com for specific Pb−free orderable part numbers, or contact your local ON Semiconductor sales office or representative.**

PNP
2N5684
NPN
2N5686

50 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
60 − 80 VOLTS
300 WATTS



CASE 197A−05
TO−204AE

MAXIMUM RATINGS (1)

Rating	Symbol	2N5684 2N5686	Unit
Collector−Emitter Voltage	V_{CEO}	80	Vdc
Collector−Base Voltage	V_{CB}	80	Vdc
Emitter−Base Voltage	V_{EB}	5.0	Vdc
Collector Current − Continuous	I_C	50	Adc
Base Current	I_B	15	Adc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	300 1.715	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS (1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	0.584	°C/W

(1) Indicates JEDEC Registered Data.

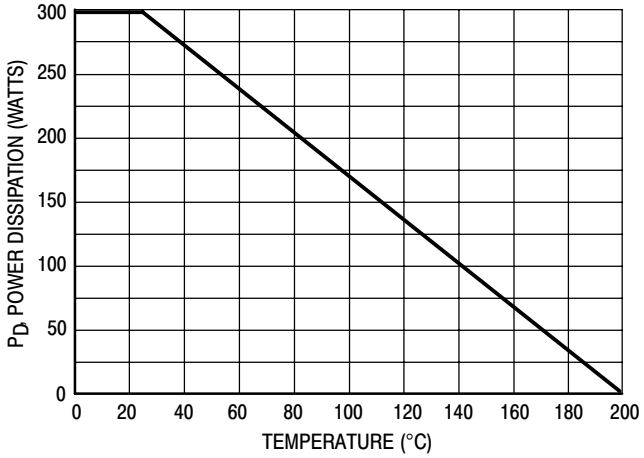


Figure 1. Power Derating

Safe Area Curves are indicated by Figure 5. All limits are applicable and must be observed.

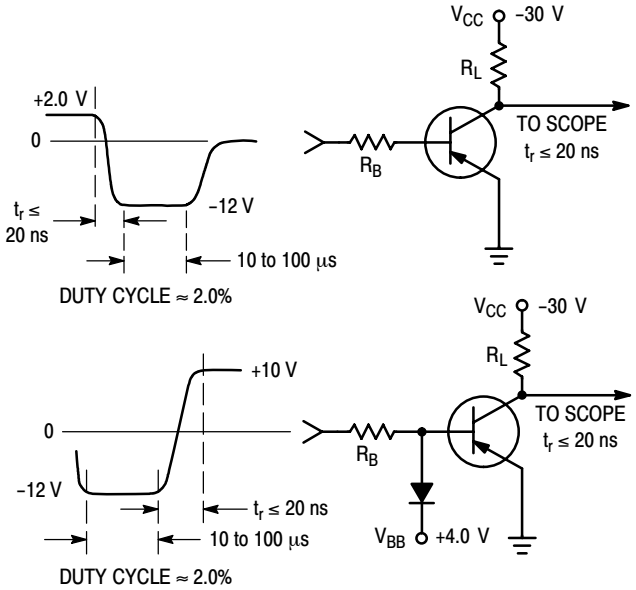
March, 2006 − Rev. 11
Publication Order Number:
2N5684/D

***ELECTRICAL CHARACTERISTICS** (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Sustaining Voltage (Note 2) (I_C = 0.2 Adc, I_B = 0)	$V_{CEO(sus)}$	80	–	Vdc
Collector Cutoff Current (V_{CE} = 40 Vdc, I_B = 0)	I_{CEO}	–	1.0	mAdc
Collector Cutoff Current (V_{CE} = 80 Vdc, $V_{EB(off)}$ = 1.5 Vdc) (V_{CE} = 80 Vdc, $V_{EB(off)}$ = 1.5 Vdc, T_C = 150°C)	I_{CEX}	– –	2.0 10	mAdc
Collector Cutoff Current (V_{CB} = 80 Vdc, I_E = 0)	I_{CBO}	–	2.0	mAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	–	5.0	mAdc
ON CHARACTERISTICS				
DC Current Gain (Note 2) (I_C = 25 Adc, V_{CE} = 2.0 Vdc) (I_C = 50 Adc, V_{CE} = 5.0 Vdc)	h_{FE}	15 5.0	60 –	–
Collector−Emitter Saturation Voltage (Note 2) (I_C = 25 Adc, I_B = 2.5 Adc) (I_C = 50 Adc, I_B = 10 Adc)	$V_{CE(sat)}$	– –	1.0 5.0	Vdc
Base−Emitter Saturation Voltage (Note 1) (I_C = 25 Adc, I_B = 2.5 Adc)	$V_{BE(sat)}$	–	2.0	Vdc
Base−Emitter On Voltage (Note 1) (I_C = 25 Adc, V_{CE} = 2.0 Vdc)	$V_{BE(on)}$	–	2.0	Vdc
DYNAMIC CHARACTERISTICS				
Current−Gain − Bandwidth Product (I_C = 5.0 Adc, V_{CE} = 10 Vdc, f = 1.0 MHz)	f_T	2.0	–	MHz
Output Capacitance 2N5684 (V_{CB} = 10 Vdc, I_E = 0, f = 0.1 MHz) 2N5686	C_{ob}	– –	2000 1200	pF
Small−Signal Current Gain (I_C = 10 Adc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{fe}	15	–	

*Indicates JEDEC Registered Data.

Note 2: Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.



FOR CURVES OF FIGURES 3 & 6, R_B & R_L ARE VARIED.
INPUT LEVELS ARE APPROXIMATELY AS SHOWN.
FOR NPN CIRCUITS, REVERSE ALL POLARITIES.

Figure 2. Switching Time Test Circuit

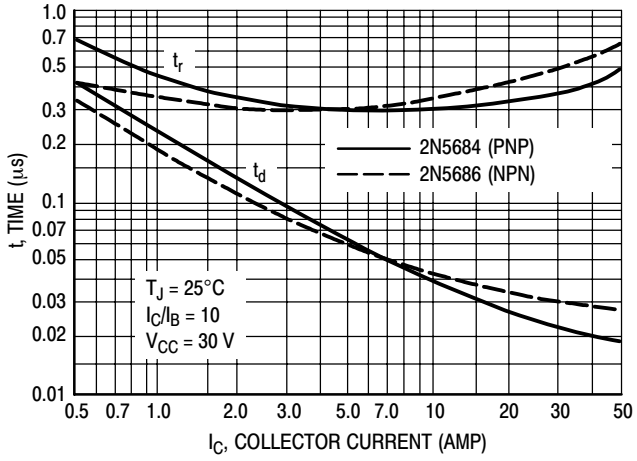


Figure 3. Turn−On Time

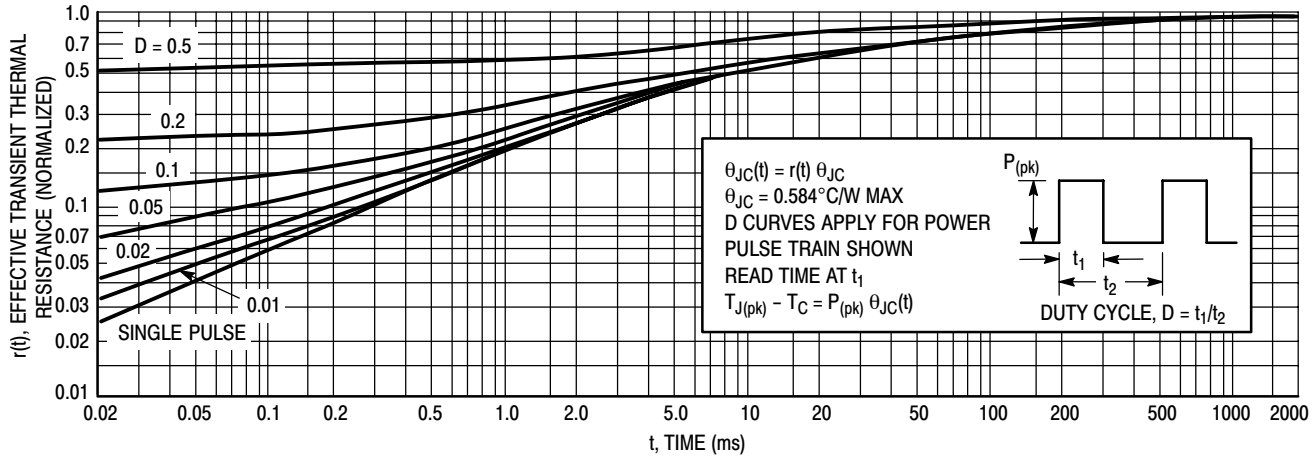


Figure 4. Thermal Response

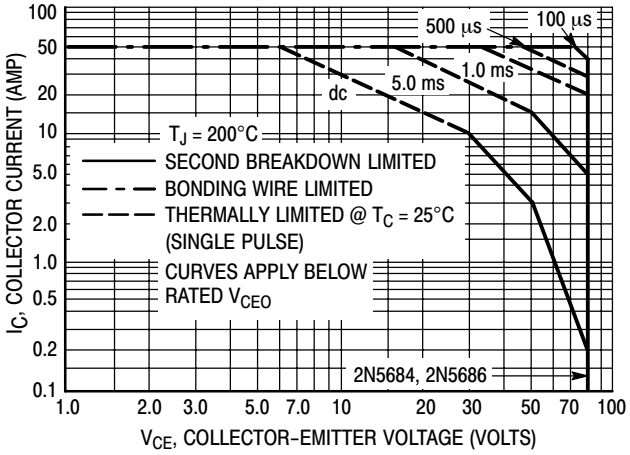


Figure 5. Active−Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 200°C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 200°C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

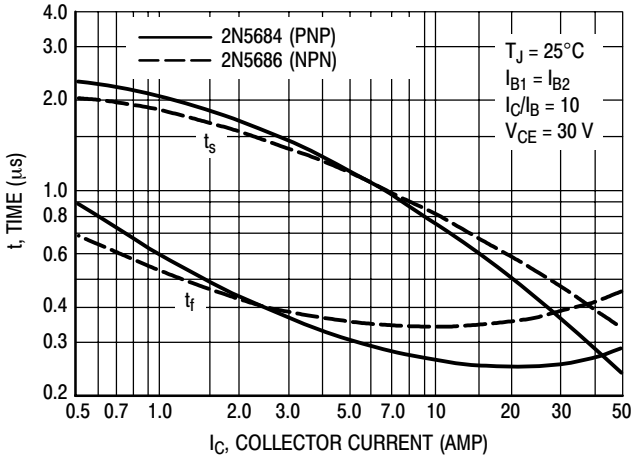


Figure 6. Turn−Off Time

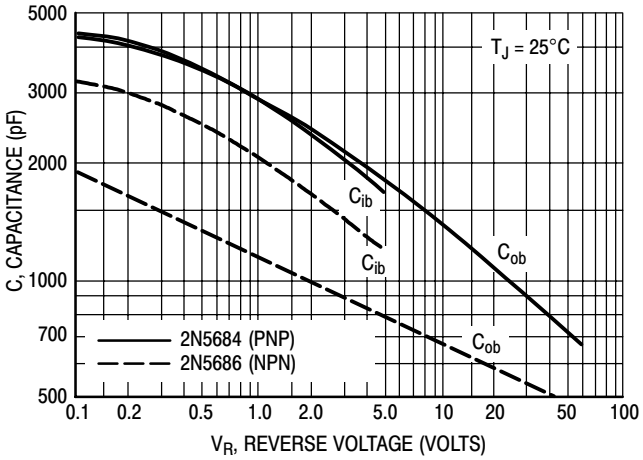
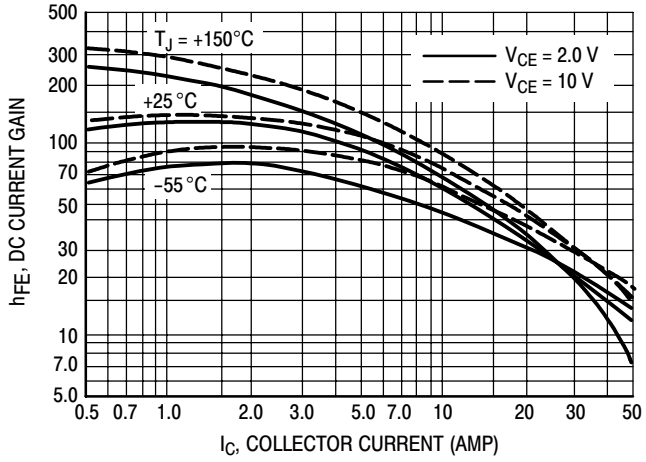


Figure 7. Capacitance

PNP
2N5684



NPN
2N5686

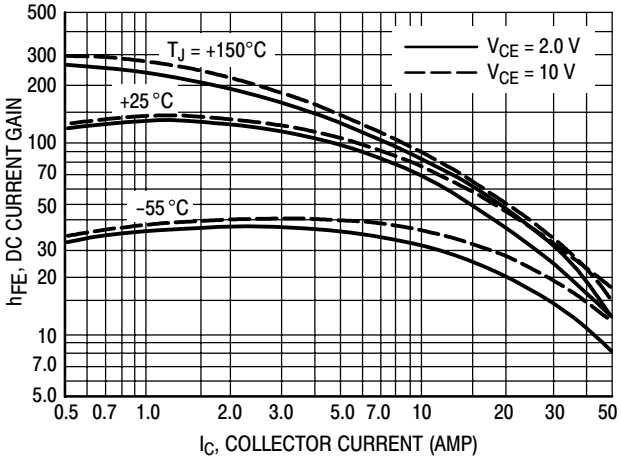
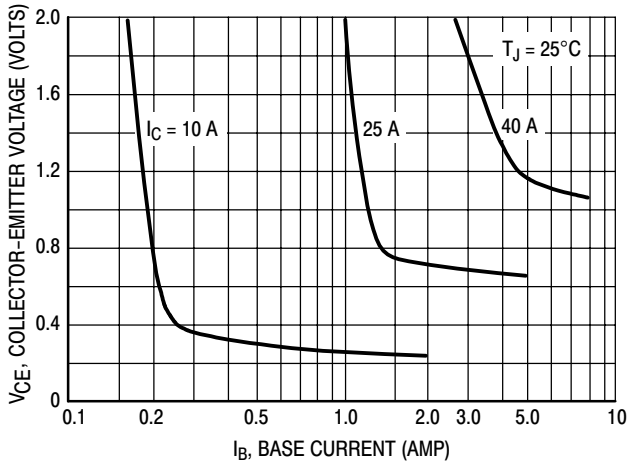


Figure 8. DC Current Gain



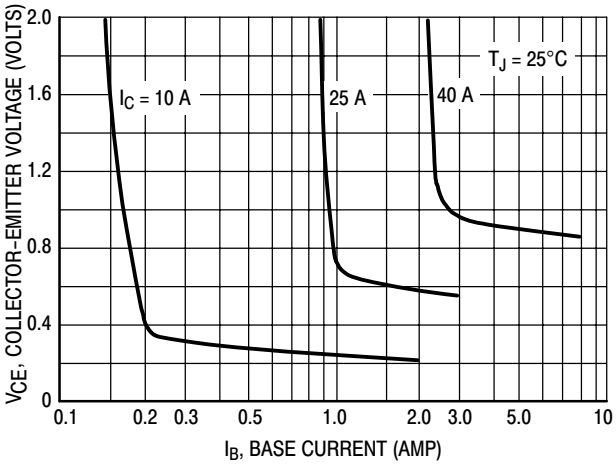
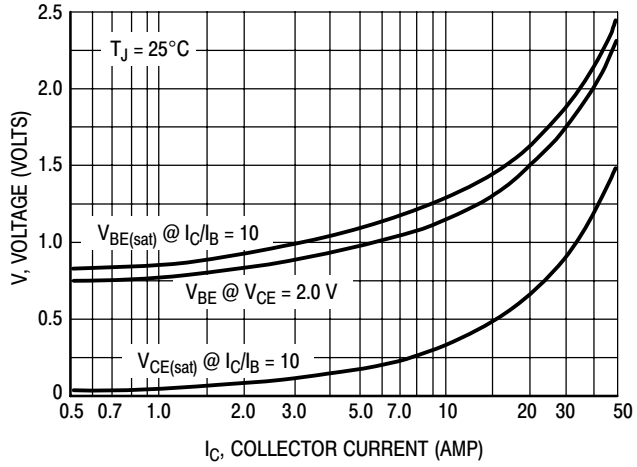


Figure 9. Collector Saturation Region



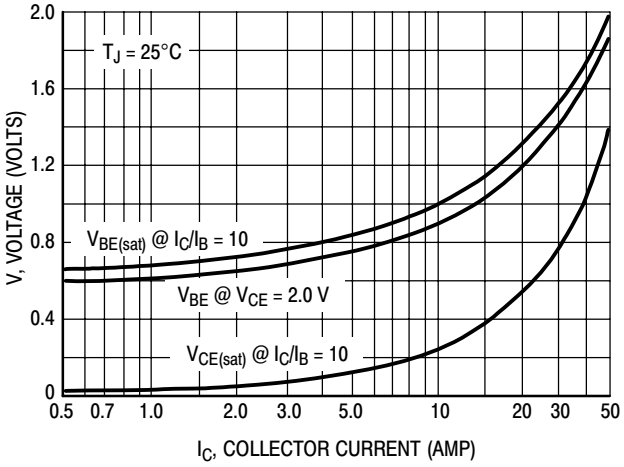


Figure 10. “On” Voltages

PACKAGE DIMENSIONS

CASE 197A−05
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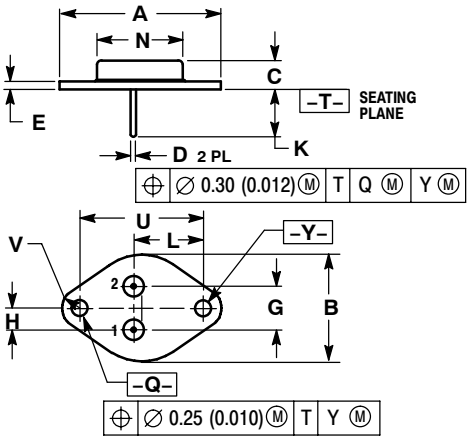
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	1.530 REF		38.86 REF	
B	0.990	1.050	25.15	26.67
C	0.250	0.335	6.35	8.51
D	0.057	0.063	1.45	1.60
E	0.060	0.070	1.53	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	0.760	0.830	19.31	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

Notes

Notes

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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